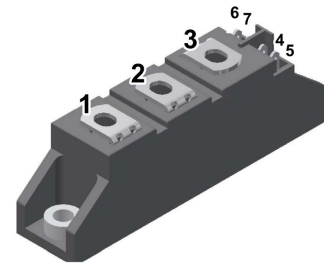


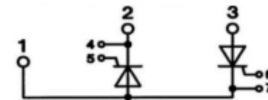
PRODUCT FEATURES

- DBC Al2O3-ceramic
- Advanced power cycling
- Low Leakage Current
- Glass passivation thyristor chips



APPLICATIONS

- Line rectifying 50/60 Hz
- Softstart AC motor control
- AC power control
- Lighting and temperature control
- Temperature control



ABSOLUTE MAXIMUM RATINGS(T_C =25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Values	Unit
V _{RRM}	Maximum Repetitive Reverse Voltage	T _{vj} =125°C	1600	V
V _{DRM}	Maximum repetitive peak off-state voltage			
V _{RSM}	Non-Repetitive Reverse Voltage	T _{vj} =125°C	1700	V
V _{DSM}	Non-repetitive peak off-state voltage			
I _{RRM}	Maximum Repetitive Reverse Current	T _{vj} =125°C	10	mA
I _{DRM}	Maximum repetitive peak off-state Current			
I _{T(AV)}	Mean On-state Current	T _C =85°C	140	A
I _{RMS}	RMS Current	T _C =85°C, sin180°	220	
I _{TSM}	Non Repetitive Surge Peak On-state Current	10ms, T _j =25°C	2700	
I ² t	For Fusing	10ms, T _j =25°C	36.45	
V _{TM}	Peak on-state voltage	V _{TM} =150A	1.30	V
dv/dt	critical rate of rise of off-state voltage. Min	V _d =2/3V _{DRM} Gate Open T _j =125°C	1000	V/us
I _{GT}	gate trigger current max. VD=12V R =140 Ω		100	mA
V _{GT}	gate trigger voltage max. VD=12V R =140 Ω		2.5	V
I _H	gate trigger current		220	mA
I _L	latching current		300	mA
Viso	AC 50Hz RMS 1min		2500	V
T _J	Junction Temperature		-40 to +125	°C
T _{STG}	Storage Temperature Range		-40 to +125	
R _{thJC}	Junction to Case Thermal Resistance(Per thyristor chip)		0.22	°C /W
R _{thCH}	Case to heatsink Thermal Resistance		0.2	°C /W
mounting torque	Module to Sink M5		2.5--4	Nm
	Terminal M5		2.5--4	Nm

Outlines

